

Elektrische Eigenschaften**Electrical properties****Höchstzulässige Werte****Maximum rated values**

Periodische Vorwärts- und Rückwärts-Spitzensperrspannung	repetitive peak forward off-state and reverse voltages	$t_{vj} = -40^{\circ}\text{C} \dots t_{vj\text{max}}$	$V_{\text{DRM}}, V_{\text{RRM}}$ 800, 1000 V 1100, 1200 V 1300* V
Vorwärts-Stoßspitzensperrspannung	non repetitive peak forward off-state voltage	$t_{vj} = -40^{\circ}\text{C} \dots t_{vj\text{max}}$	$V_{\text{DSM}} = V_{\text{DRM}}$
Rückwärts-Stoßspitzensperrspannung	non repetitive peak reverse voltage	$t_{vj} = +25^{\circ}\text{C} \dots t_{vj\text{max}}$	$V_{\text{RSM}} = V_{\text{RRM}}$ + 100 V
Durchlaßstrom-Grenzwert	RMS on-state current	$t_c = 85^{\circ}\text{C}$	I_{TRMSM} 550 A
Dauerstrom	average on-state current	$t_c = 73^{\circ}\text{C}$	I_{TAVM} 290 A 350 A
Stoßstrom-Grenzwert	surge current	$t_{vj} = 25^{\circ}\text{C}, t_p = 10 \text{ ms}$ $t_{vj} = t_{vj\text{max}}, t_p = 10 \text{ ms}$	I_{TSM} 7200 A 6400 A
Grenzlastintegral	I^2t -value	$t_{vj} = 25^{\circ}\text{C}, t_p = 10 \text{ ms}$ $t_{vj} = t_{vj\text{max}}, t_p = 10 \text{ ms}$	I^2t 260 kA^2s 205 kA^2s
Kritische Stromsteilheit	critical rate of rise of on-state current	$v_D \leq 67\% V_{\text{DRM}}, f = 50 \text{ Hz}$ $I_{\text{GM}} = 1 \text{ A}, di_G/dt = 1 \text{ A}/\mu\text{s}$	$(di/dt)_{\text{cr}}$ 200 $\text{A}/\mu\text{s}$
Kritische Spannungssteilheit	critical rate of rise of off-state voltage	$t_{vj} = t_{vj\text{max}}, v_D = 67\% V_{\text{DRM}}$	$(dv/dt)_{\text{cr}}$ B: 50 50 $\text{V}/\mu\text{s}$ c*: 500 500 $\text{V}/\mu\text{s}$ L: 500 50 $\text{V}/\mu\text{s}$ M*: 1000 500 $\text{V}/\mu\text{s}$

Charakteristische Werte**Characteristic values**

Durchlaßspannung	on-state voltage	$t_{vj} = t_{vj\text{max}}, I_T = 1000 \text{ A}$	V_T max. 2,1 V
Schleusenspannung	threshold voltage	$t_{vj} = t_{vj\text{max}}$	$V_{T(\text{TO})}$ 1,2 V
Ersatzwiderstand	slope resistance	$t_{vj} = t_{vj\text{max}}$	r_T 0,75 $\text{m}\Omega$
Zündstrom	gate trigger current	$t_{vj} = 25^{\circ}\text{C}, v_D = 12 \text{ V}$	I_{GT} max. 250 mA
Zündspannung	gate trigger voltage	$t_{vj} = 25^{\circ}\text{C}, v_D = 12 \text{ V}$	V_{GT} max. 2,2 V
Nicht zündender Steuerstrom	gate non-trigger current	$t_{vj} = t_{vj\text{max}}, v_D = 12 \text{ V}$	I_{GD} max. 10 mA
Nicht zündende Steuerspannung	gate non-trigger voltage	$t_{vj} = t_{vj\text{max}}, v_D = 0,5 V_{\text{DRM}}$	V_{GD} max. 0,25 V
Haltestrom	holding current	$t_{vj} = 25^{\circ}\text{C}, v_D = 12 \text{ V}, R_A = 10 \Omega$	I_H max. 250 mA
Einraststrom	latching current	$t_{vj} = 25^{\circ}\text{C}, v_D = 12 \text{ V}, R_{\text{GK}} \geq 10 \Omega$ $I_{\text{GM}} = 1 \text{ A}, di_G/dt = 1 \text{ A}/\mu\text{s}, t_g = 20 \mu\text{s}$	I_L max. 1 A
Vorwärts- u. Rückwärts-Sperrstrom	forward off-state and reverse Currents	$t_{vj} = t_{vj\text{max}}, v_D = V_{\text{DRM}}, v_R = V_{\text{RRM}}$	i_D, i_R max. 50 mA
Zündverzögerung	gate controlled delay time	$t_{vj} = 25^{\circ}\text{C}, I_{\text{GM}} = 1 \text{ A}, di_G/dt = 1 \text{ A}/\mu\text{s}$	t_{gd} max. 1,2 μs
Freiwerdezeit	circuit commutated turn-off time	siehe Techn. Erl./see Techn. Inf.	t_q s: max. 18 μs E: max. 20 μs F: max. 25 μs

Thermische Eigenschaften**Thermal properties**

Innerer Wärmewiderstand	thermal resistance, junction to case	$\Theta = 180^{\circ}\text{el, sin}$ DC	R_{thJC} max. 0,08 $^{\circ}\text{C}/\text{W}$ max. 0,077 $^{\circ}\text{C}/\text{W}$
Höchstzul. Sperrschichttemperatur	max. junction temperature		$t_{vj\text{max}}$ 125 $^{\circ}\text{C}$
Betriebstemperatur	Operating temperature		$t_{\text{c op}}$ -40 ... + 125 $^{\circ}\text{C}$
Lagertemperatur	storage temperature		t_{stg} -40 ... + 150 $^{\circ}\text{C}$

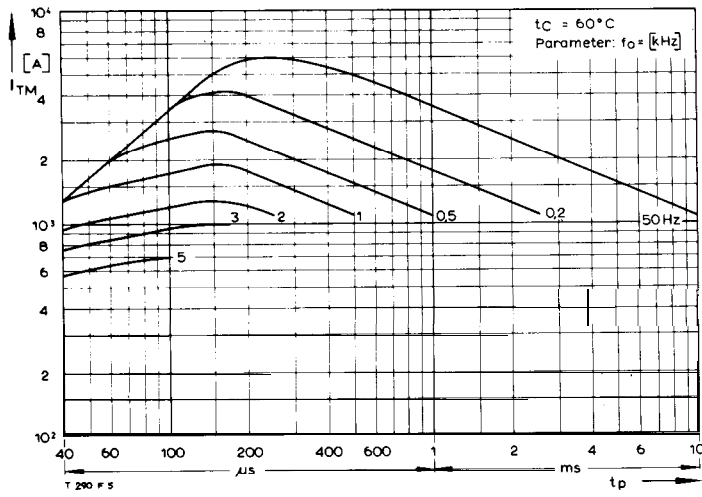
Mechanische Eigenschaften**Mechanical properties**

Si-Element mit Druckkontakt	Si-pellet with pressure contact		F 5,5 kN
Anpreßkraft	Clamping force		G typ. 630 g
Gewicht	weight		14 mm
Kriechstrecke	Creepage distance		C
Feuchteklasse	humidity classification	DIN 40040	50 m/s^2
Schwingfestigkeit	Vibration resistance	f = 50 Hz	Seitelpage 154
Maßbild B	outline B	DIN 41894-224A4	

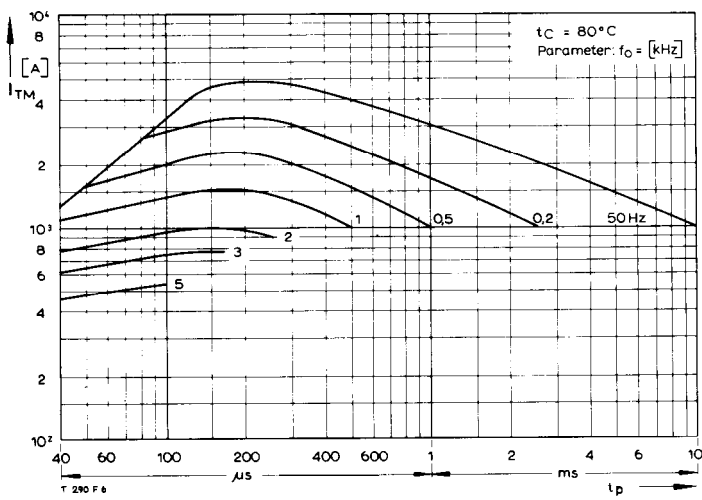
* Für größere Stückzahlen bitte Liefertermin erfragen/Delivery for larger quantities on request

1) Werte nach DIN IEC 747-6 (ohne vorausgehende Kommutierung)/Values to DIN IEC 747-6 (without prior commutation)

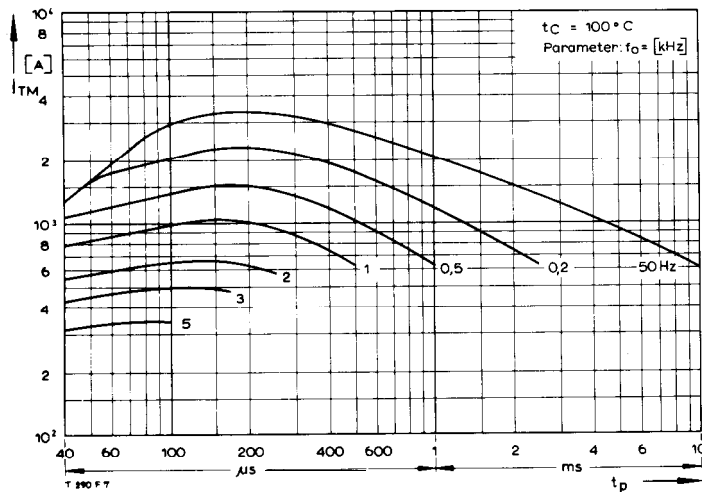
2) Unmittelbar nach der Freiwerdezeit, vgl. Meßbedingungen für t_q /Immediately after circuit commutated turn-off time, see Parameters t_q



Bild/ Fig. 1



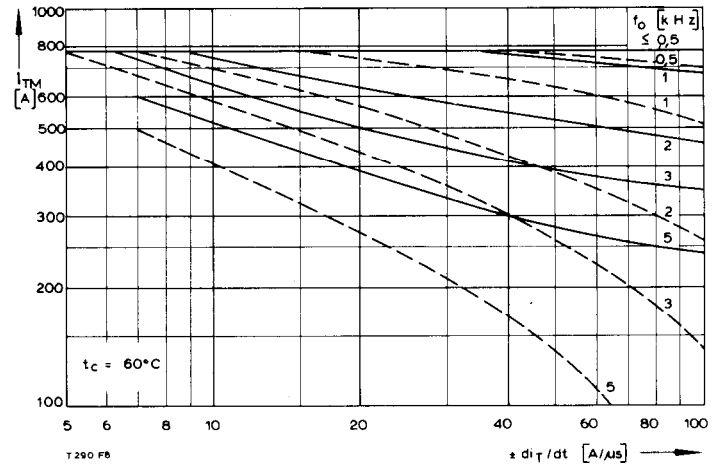
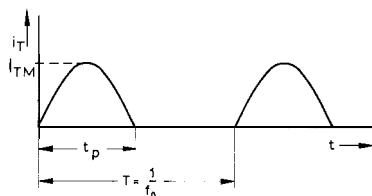
Bild/ Fig. 2



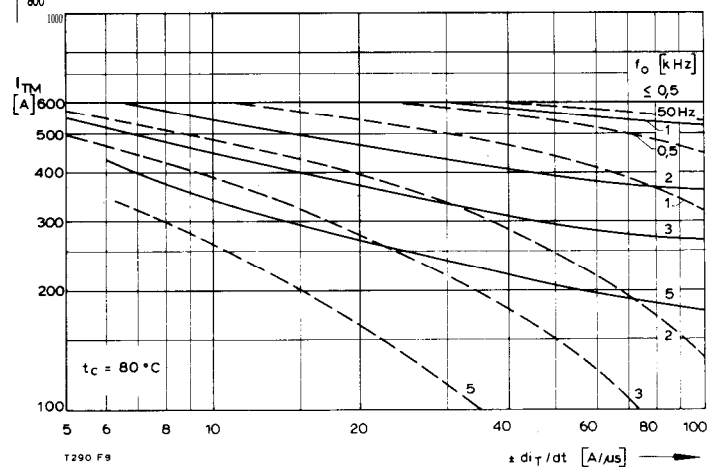
Bild/ Fig. 3

Bild/ Fig. 1, 2, 3
Steuergenerator/pulse generator:
 $i_G = 1 \text{ A}$, $di_G/dt = 1 \text{ A}/\mu\text{s}$

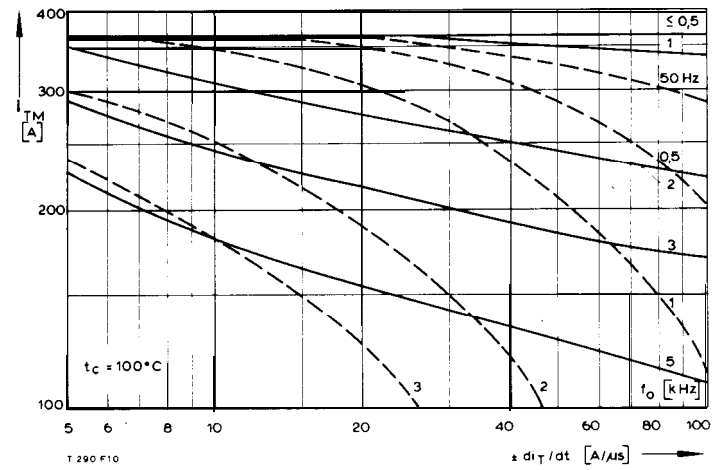
RC-Glied/RC-network:
 $R[\Omega] \geq 0,02 \text{ VDM [V]}$
 $C \leq 0,22 \mu\text{F}$
 $V_{DM} \leq 0,67 \text{ V}_{DRM}$



Bild/ Fig. 4



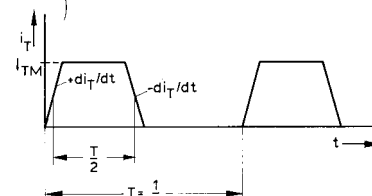
Bild/ Fig. 5

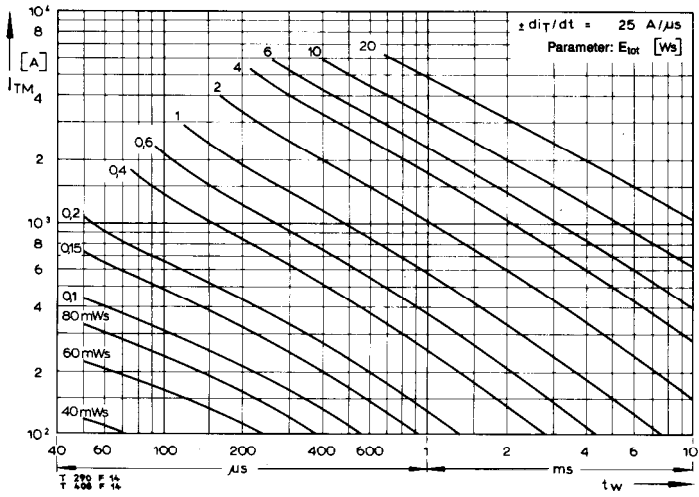


Bild/ Fig. 6

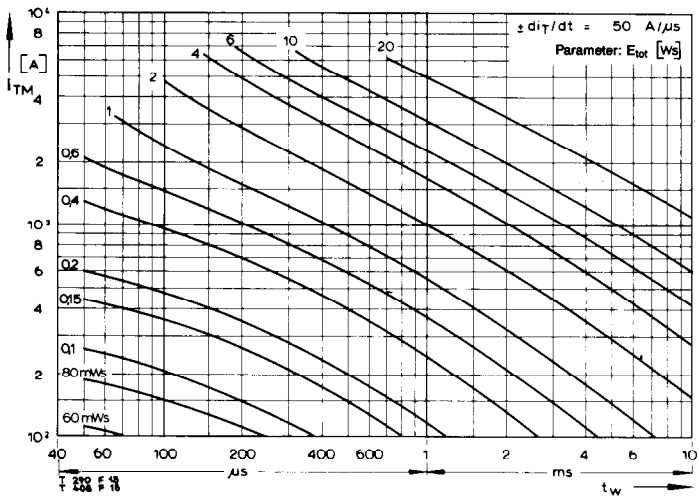
Bild/ Fig. 4, 5, 6
Steuergenerator/pulse generator:
 $i_G = 1 \text{ A}$, $di_G/dt = 1 \text{ A}/\mu\text{s}$

RC-Glied/RC-network:
 $R[\Omega] \geq 0,02 \text{ VDM [V]}$
 $C \leq 0,33 \text{ pF}$
 $V_{DM} \leq 0,67 \text{ V}_{DRM}$
 $dv_G/dt \leq 600 \text{ V}/\mu\text{s}$
 $V_{RM} \leq 0,67 \text{ V}_{RRM}$

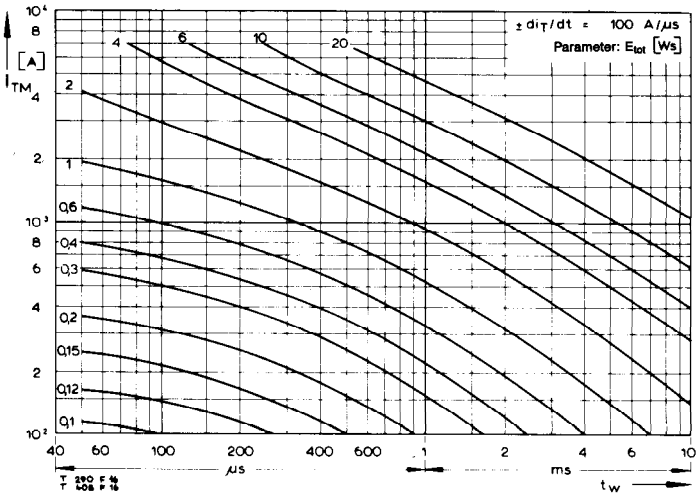




Bild/Fig. 10

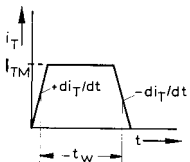


Bild/Fig. 11

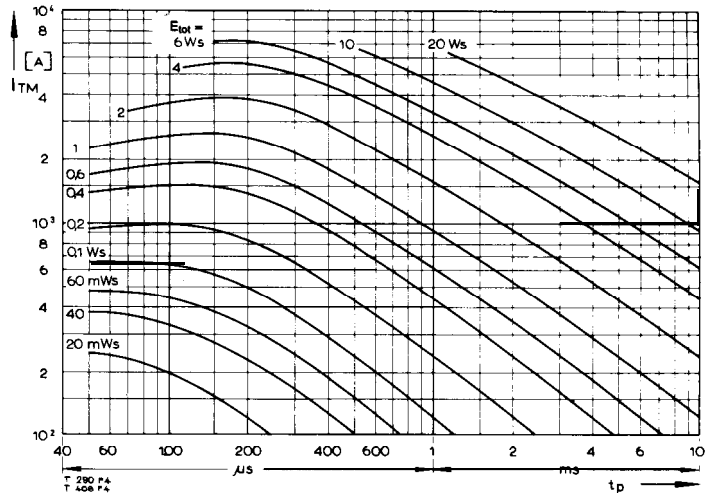


Bild/Fig. 12

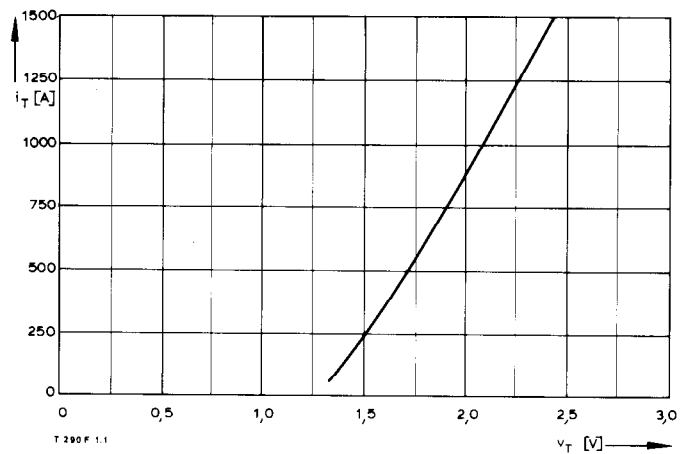
Bild/Fig. 10, 11, 12
Steuer-generator/pulse generator:
 $i_G = 1 \text{ A}$, $di_G/dt = 1 \text{ A}/\mu\text{s}$



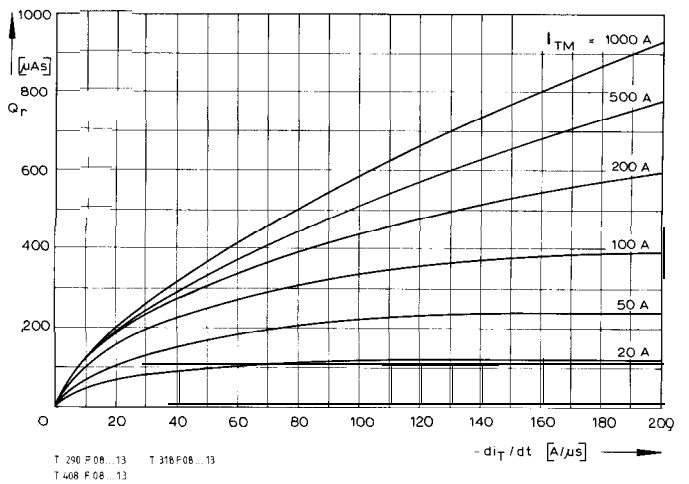
RC-Glied/RC-network:
 $R [\Omega] \geq 0,02 v_{DM} [V]$
 $C \leq 0,33 \mu\text{F}$
 $v_{DM} \leq 0,67 v_{DRM}$
 $dv_R/dt \leq 600 \text{ V}/\mu\text{s}$
 $v_{RM} \leq 0,67 v_{RRM}$



Bild/Fig. 13

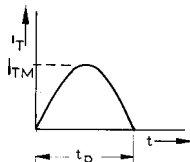


Bild/Fig. 14

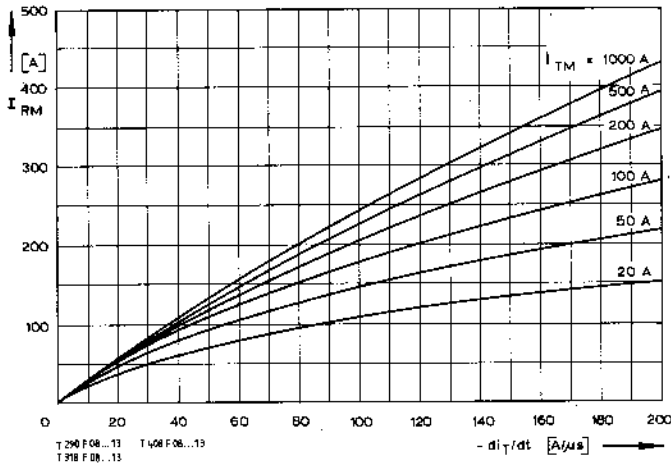


Bild/Fig. 15

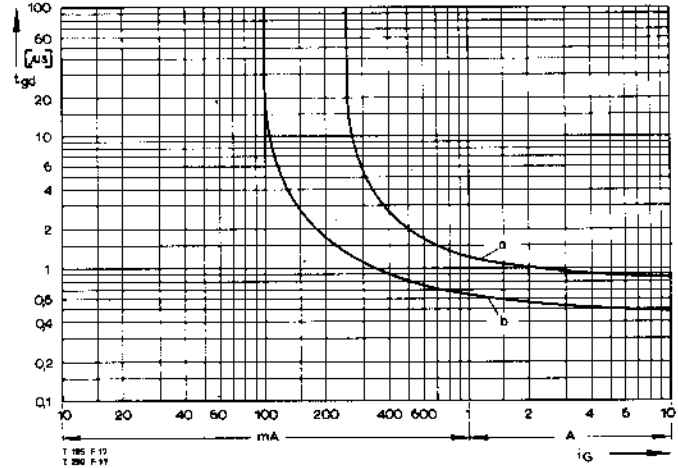
(zu Bild/to Fig. 13)
Steuer-generator/pulse generator:
 $i_G = 1 \text{ A}$, $di_G/dt = 1 \text{ A}/\mu\text{s}$



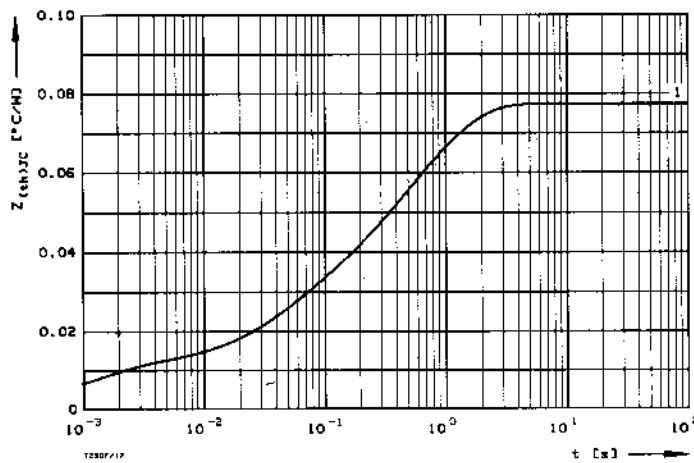
RC-Glied/RC-network:
 $FI [\Omega] \geq 0,02 v_{DM} [V]$
 $C \leq 0,22 \mu\text{F}$



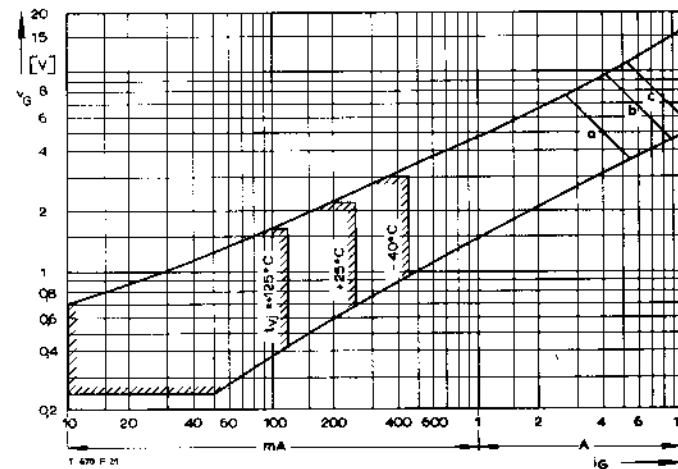
Bild/Fig. 16
 Rückstromspitze $I_{RM} = f(-di/dt)$, $t_{vj} = t_{vj(max)}$, $V_R = 0,5 V_{RRM}$, $V_{RM} = 0,8 V_{RRM}$
 Peak reverse recovery current $I_{RM} = f(-di/dt)$, $t_{vj} = t_{vj(max)}$, $V_R = 0,5 V_{RRM}$, $V_{RM} = 0,8 V_{RRM}$
 Parameter: Durchlaßstrom/On-state current I_{TM}



Bild/Fig. 18
 Zündverzugs/Gate controlled delay time $t_{gd} = f(I_{GM})$, $t_{vj} = 25^\circ\text{C}$, $di_G/dt = I_{GM}/1 \mu\text{s}$
 a – Maximaler Verlauf/Limiting characteristic
 b – Typischer Verlauf/Typical characteristic



Bild/Fig. 17
 Transienter innerer Wärmewiderstand $Z_{thJC} = f(t)$, DC
 Transient thermal impedance $Z_{thJC} = f(t)$, DC
 1 Beidseitige Kühlung/two-sided cooling



Bild/Fig. 19
 Steuercharakteristik mit Zündbereichen/Gate characteristic with triggering areas
 $V_G = f(I_G)$, $V_G = 12 \text{ V}$

Parameter:	a	b	c
Steuerimpulsdauer/Trigger pulse duration t_G [ms]	10	1	0,5
Höchstzulässige Spitzensteuerverlustleistung/ Max. rated peak gate power dissipation P_{GM} [W]	20	40	60

Analytische Elemente des transienten Wärmewiderstandes Z_{thJC} für DC
 Analytical elements of transient thermal impedance Z_{thJC} for DC

Pos. n	1	2	3	4	5	6	7
R_{thn} [°C/W]	0,010579	0,014042	0,016802	0,035980			
τ_n [s]	0,001165	0,040454	0,222096	0,838218			

Analytische Funktion/analytical function:

$$Z_{thJC} = \sum_{n=1}^{n_{max}} R_{thn} (1 - \text{EXP}(-t/\tau_n))$$